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(57) Abstract :

The present invention relates to a method for fabricating a perovskite solar cell with enhanced light-absorbing properties is disclosed. The method involves the use of a textured surface layer comprising MgF₂, a front contact layer comprising ITO of 100 nm, and a rear contact layer comprising gold of 20 nm. The textured surface layer is processed to form pyramids on the front surface, enhancing light absorption. The device is illuminated from the ETL side under the AM1.5G light spectrum, resulting in improved surface electron current density and optical intensity.

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